

ANGI140180-P47

X-Band matched GaN Device

Features:

Frequency: 14~18GHz

Saturated Output Power: $P_{sat}=47\text{dBm}(\text{type})$

PowerGain: $\text{Gain} \geq 21\text{dB}$

Efficiency: $\geq 35\%$

Port Matching: $Z_{in}/Z_{out}=50\Omega$

Description:

ANGI140180-P47 is an internal matching GaN device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 14~18GHz. This device can be used in different RF/Microwave system and subsystem.

The high output power level, high efficiency and wide operating temperature range can make application very flexible.

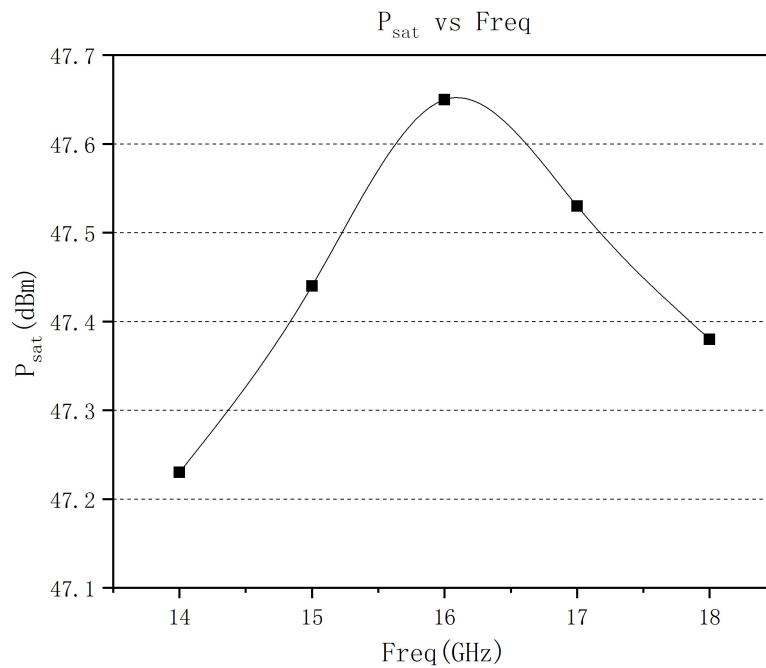
Maximun Ratings (TC=25°C, Not recommended working under this condition):

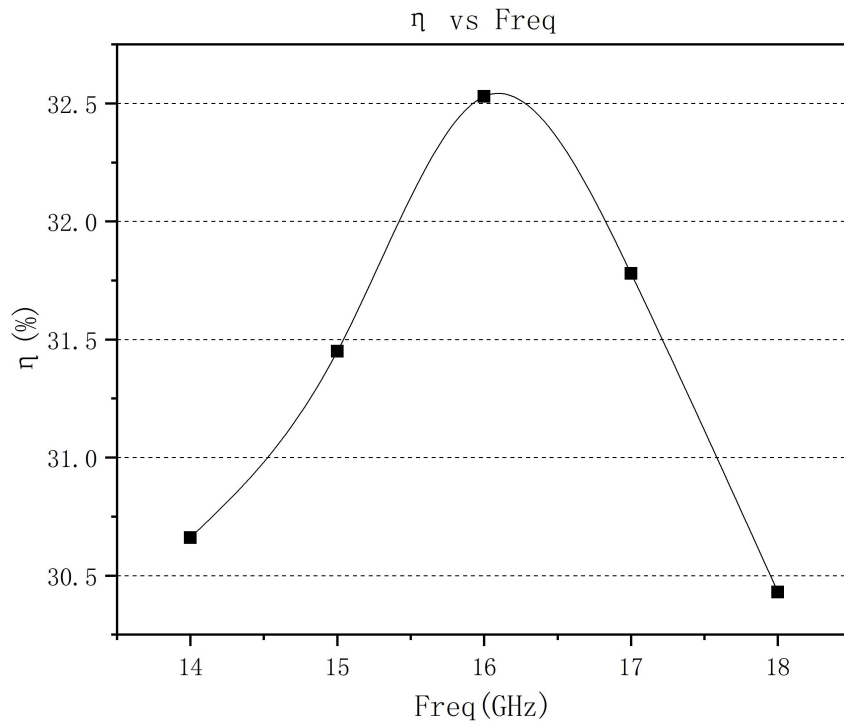
	Symbol	Value	Unit
Voltage between source and drain	V_{DS}	40	V
Voltage between gate and source	V_{GS}	-5	V
Storage Temperature Range	T_{stg}	-65 to +175	°C
Drain and Source Channel Temperature	T_{ch}	175	°C

Electrical Characteristics:

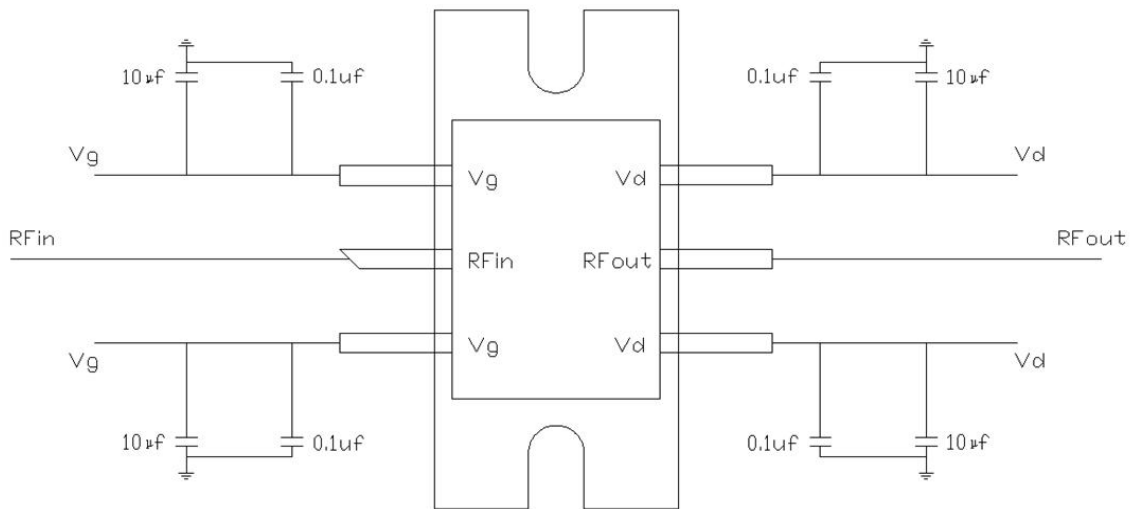
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I_{dsr}	$V_{ds}=28V$ PW. $T=1ms, Duty=10\%$ $P_{in}: 26dBm$ $Freq: 14\sim 18GHz$	-	6.2	-	A
Saturated Output Power	P_{sat}		-	47	-	dBm
Gain	G_p		21	-	-	dB
Efficiency			30	-	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





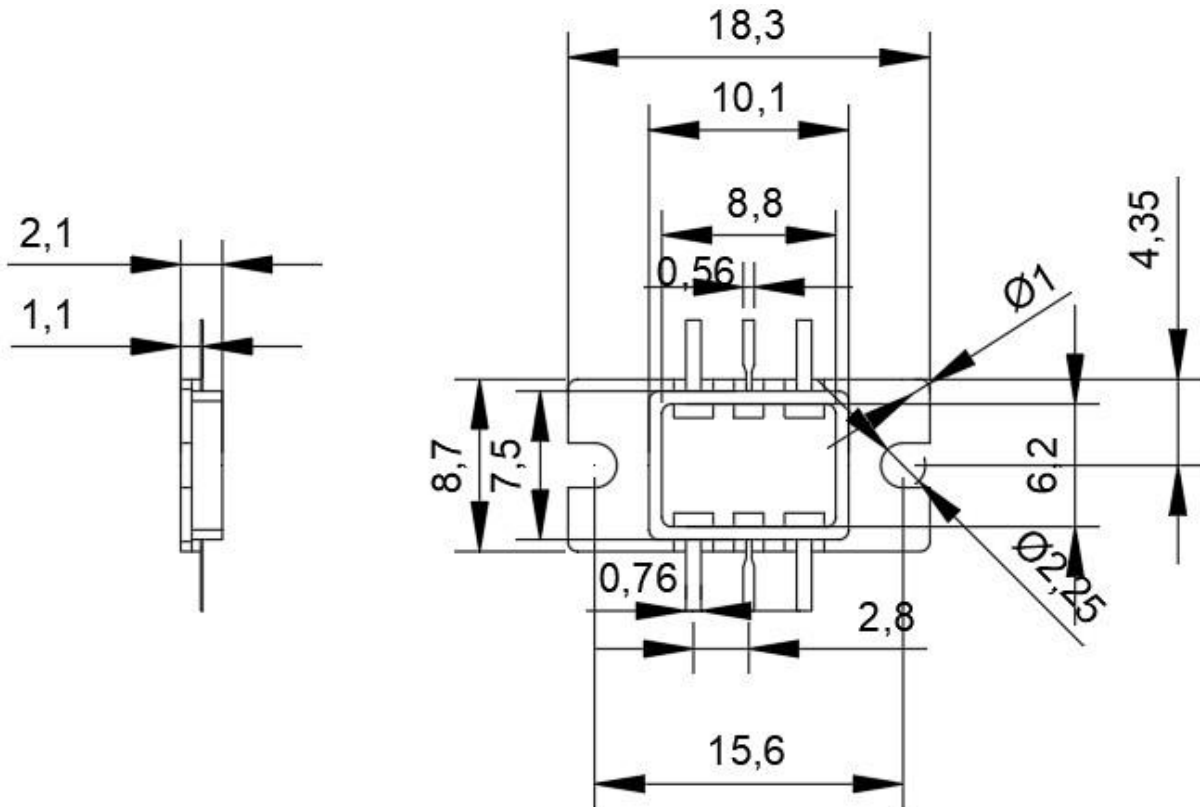
Application Circuit:



ESD Level:

ESD	Class III	2000V
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Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.